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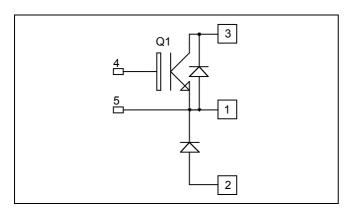
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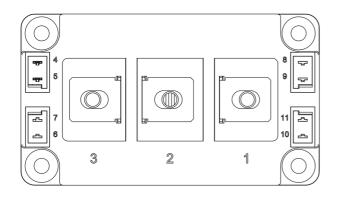
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Buck Chopper Trench + Field Stop IGBT3 Power Module





APTGT300SK60D3G

$$V_{CES} = 600V$$

 $I_C = 300A$ @ Tc = 80°C

Application

- AC and DC motor control
- Switched Mode Power Supplies

Features

- Trench + Field Stop IGBT3 Technology
 - Low voltage drop
 - Low tail current
 - Switching frequency up to 20 kHz
 - Soft recovery parallel diodes
 - Low diode VF
 - Low leakage current
 - RBSOA and SCSOA rated
 - Kelvin emitter for easy drive
- High level of integration
- M6 power connectors

Benefits

- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive T_C of V_{CEsat}
- RoHS Compliant

Absolute maximum ratings

Symbol	Parameter		Max ratings	Unit
V _{CES}	Collector - Emitter Breakdown Voltage		600	V
т	Continuous Collector Current	$T_C = 25^{\circ}C$	400	
I _C	Continuous Concetor Current	$T_C = 80^{\circ}C$	300	А
I _{CM}	Pulsed Collector Current	$T_C = 25^{\circ}C$	600	
V_{GE}	Gate – Emitter Voltage		± 20	V
PD	Maximum Power Dissipation	$T_C = 25^{\circ}C$	940	W
RBSOA	Reverse Bias Safe Operating Area	$T_j = 125^{\circ}C$	600A @ 520V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

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All ratings (a) $T_j = 25^{\circ}C$ unless otherwise specified

Electrical Unaracteristics								
Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit	
I _{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 600V$				500	μA	
V	Collector Emitter saturation Voltage	$V_{GE} = 15V$	$T_j = 25^{\circ}C$		1.5	1.9	V	
V _{CE(sat)}	Conector Emitter saturation voltage	$I_{\rm C} = 300 {\rm A}$ $T_{\rm j} = 150^{\circ} {\rm C}$		1.7		v		
V _{GE(th)}	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 4.8 \text{ mA}$		5.0	5.8	6.5	V	
I _{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$				400	nA	

Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Тур	Max	Unit
Cies	Input Capacitance	$V_{GE} = 0V$		18.5		
Coes	Output Capacitance	$V_{CE} = 25V$		1.2		nF
C _{res}	Reverse Transfer Capacitance	f = 1 MHz		0.5		
Q _G	Gate charge	V _{GE} =±15V, I _C =300A V _{CE} =300V		3.2		μC
T _{d(on)}	Turn-on Delay Time	Inductive Switching (25°C)		110		
Tr	Rise Time	$V_{GE} = \pm 15V$		50		
T _{d(off)}	Turn-off Delay Time	$V_{Bus} = 300V$ $I_{C} = 300A$		490		ns
$T_{\rm f}$	Fall Time	$R_G = 2.2\Omega$		50		
T _{d(on)}	Turn-on Delay Time	Inductive Switching (150°C)		130		
T_r	Rise Time	$V_{GE} = \pm 15V$ $V_{Bus} = 300V$		60		ns
T _{d(off)}	Turn-off Delay Time	$I_{\rm C} = 300 \text{ A}$		530		
T_{f}	Fall Time	$R_G = 2.2\Omega$		70		
Eon	Turn on Energy	$V_{GE} = \pm 15V$ $T_j = 25^{\circ}C$		3.1		
Lon	rum on Energy	$V_{Bus} = 300V$ $T_i = 150^{\circ}C$		3.3		mJ
E _{off}	Turn off Energy	$I_{\rm C} = 300 \text{A}$ $T_{\rm j} = 25^{\circ} \text{C}$		12		110
011		$R_G = 2.2\Omega$ $T_j = 150^{\circ}C$		12.5		
I _{sc}	Short Circuit data	$V_{GE} \le 15V$; $V_{Bus} = 360V$ $t_p \le 6\mu s$; $T_j = 150^{\circ}C$		1500		А

Reverse diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
V _{RRM}	Maximum Peak Repetitive Reverse Voltage			600			V
I _{RRM}	Maximum Reverse Leakage Current	V _R =600V	$T_i = 25^{\circ}C$ $T_i = 150^{\circ}C$			500 750	μΑ
I _F	DC Forward Current		$Tc = 80^{\circ}C$		300		А
$V_{\rm F}$	Diode Forward Voltage	$I_{\rm F} = 300 {\rm A}$ $V_{\rm GE} = 0 {\rm V}$	$T_i = 25^{\circ}C$ $T_i = 150^{\circ}C$		1.6 1.5	2	V
t _{rr}	Reverse Recovery Time	$I_F = 300A$ $V_R = 300V$ $di/dt = 4800A/\mu s$	$T_j = 25^{\circ}C$ $T_j = 150^{\circ}C$		100 150		ns
Q _{rr}	Reverse Recovery Charge		$T_j = 25^{\circ}C$ $T_i = 150^{\circ}C$		14.4 30.4		μC
E _{rr}	Reverse Recovery Energy		$T_j = 25^{\circ}C$ $T_j = 150^{\circ}C$		3.4 7.2		mJ

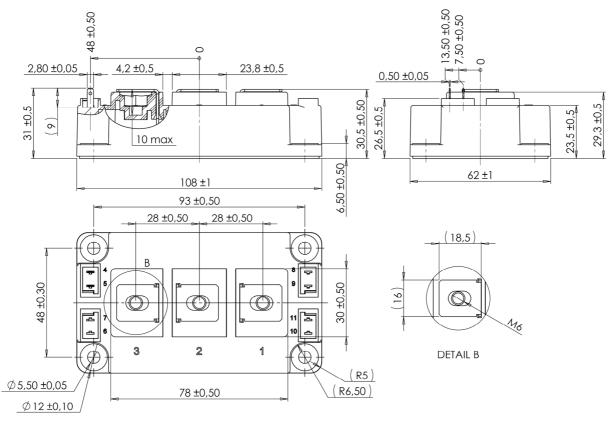


APTGT300SK60D3G

Thermal and package characteristics

Symbol	Characteristic			Min	Тур	Max	Unit
R _{thJC}	Junction to Case Thermal Resistance IGBT Diode		IGBT			0.16	°C/W
			Diode			0.25	
V _{ISOL}	RMS Isolation Voltage, any terminal to case $t = 1 \text{ min}, 50/60 \text{Hz}$			4000			V
T _J	Operating junction temperature range			-40		175	
T _{STG}	Storage Temperature Range			-40		125	°C
T _C	Operating Case Temperature			-40		125	
Torque	Mounting torque	For terminals	M6	3		5	N.m
		To Heatsink	M6	3		5	19.111
Wt	Package Weight					350	g

D3 Package outline (dimensions in mm)



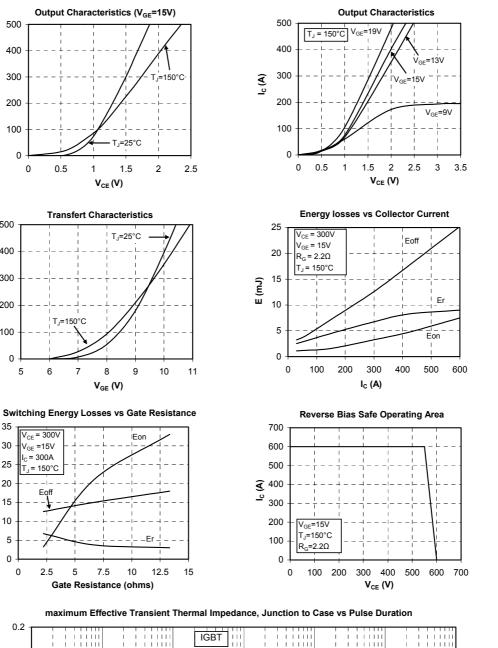


Typical Performance Curve

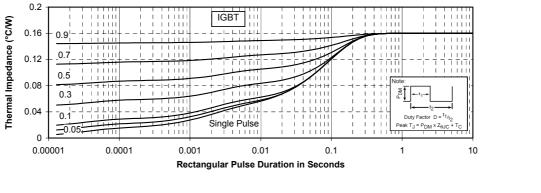
E (mJ)

I_c (A)

I_c (A)



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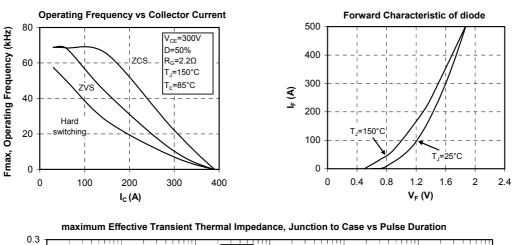


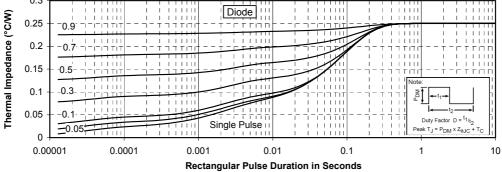
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